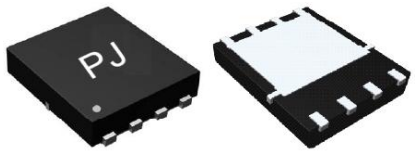
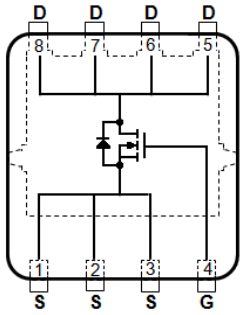
PJQ4408P

30V N-Channel Enhancement Mode MOSFET

Voltage	30 V	Current	42 A

DFN3333-8L





Features

- $R_{DS(ON)}$, V_{GS}@10V,I_D@16A<9mΩ
- $R_{DS(ON)}$, V_{GS}@4.5V,I_D@8A<13mΩ
- High switching speed
- Improved dv/dt capability
- Low Gate Charge
- Low reverse transfer capacitance
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

- Case: DFN3333-8L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.001 ounces, 0.03 grams

Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C=25°C	I_D	42	A
	T_C=100°C		26	
Pulsed Drain Current(Note 1)	T_C=25°C	I_{DM}	168	
Power Dissipation	T_C=25°C	P_D	35	W
	T_C=100°C		14	
Continuous Drain Current	T_A=25°C	I_D	10	A
	T_A=70°C		8	
Power Dissipation	T_A=25°C	P_D	2.0	W
Power Dissipation	T_A=70°C		1.3	
Operating Junction and Storage Temperature Range		T_J,T_{STG}	-55~150	°C
Typical Thermal Resistance(Note 4,5)	Junction to Case	$R_{\theta JC}$	3.6	°C/W
	Junction to Ambient	$R_{\theta JA}$	62.5	

- Limited only By Maximum Junction Temperature

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Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
Static						
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS}=0V,I_D=250uA	30	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS}=V_{GS},I_D=250uA	1.0	1.7	2.5	
Drain-Source On-State Resistance	$R_{DS(on)}$	V_{GS}=10V,I_D=16A	-	6.2	9	mΩ
		V_{GS}=4.5V,I_D=8A	-	9.6	13	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=30V,V_{GS}=0V	-	-	1.0	uA
Gate-Source Leakage Current	I_{GSS}	V_{GS}=±20V,V_{DS}=0V	-	-	±100	nA
Dynamic (Note 6)						
Total Gate Charge	Q_g	V_{DS}=15V, I_D=20A, V_{GS}=4.5V (Note 2,3)	-	7.1	-	nC
Gate-Source Charge	Q_{gs}		-	3.1	-	
Gate-Drain Charge	Q_{gd}		-	2.0	-	
Input Capacitance	Ciss	V_{DS}=25V, V_{GS}=0V, f=1.0MHZ	-	763	-	pF
Output Capacitance	Coss		-	132	-	
Reverse Transfer Capacitance	Crss		-	81	-	
Turn-On Delay Time	$td_{(on)}$	V_{DS}=15V, I_D=15A, V_{GS}=10V, R_G=6Ω (Note 2,3)	-	5.4	-	ns
Turn-On Rise Time	t_r		-	86	-	
Turn-Off Delay Time	$td_{(off)}$		-	20	-	
Turn-Off Fall Time	t_f		-	10	-	
Drain-Source Diode						
Maximum Continuous Drain-Source Diode Forward Current	I_S	---	-	-	42	A
Diode Forward Voltage	V_{SD}	I_S=1A,V_{GS}=0V	-	0.7	1.0	V

NOTES :

1. Pulse width≤300us, Duty cycle≤2%
2. Essentially independent of operating temperature typical characteristics
3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
4. The maximum current rating is package limited
5. $R_{\Theta JA}$ is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch^2 with 2oz.square pad of copper
6. Guaranteed by design, not subject to production testing.

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TYPICAL CHARACTERISTIC CURVES

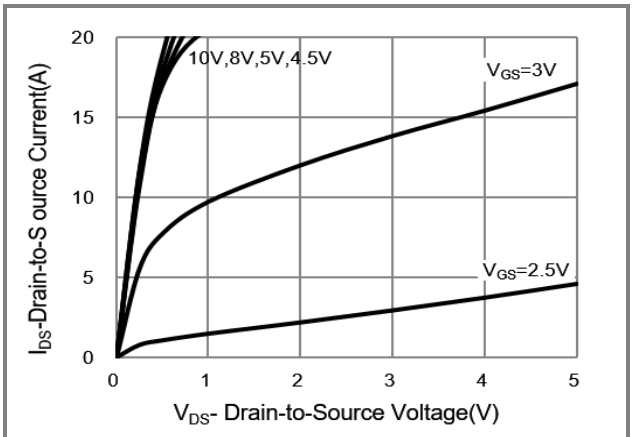

Fig.1 On-Region Characteristics

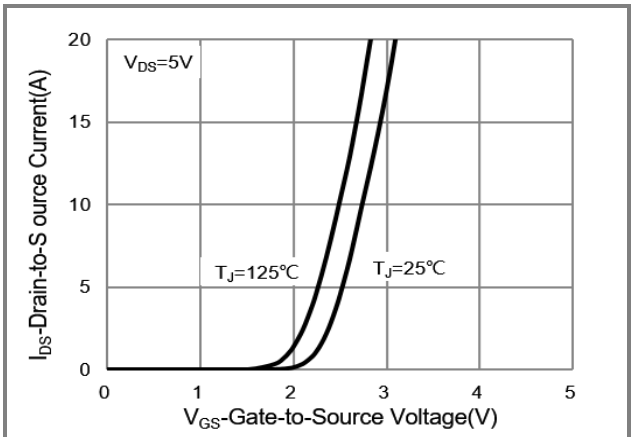

Fig.2 Transfer Characteristics

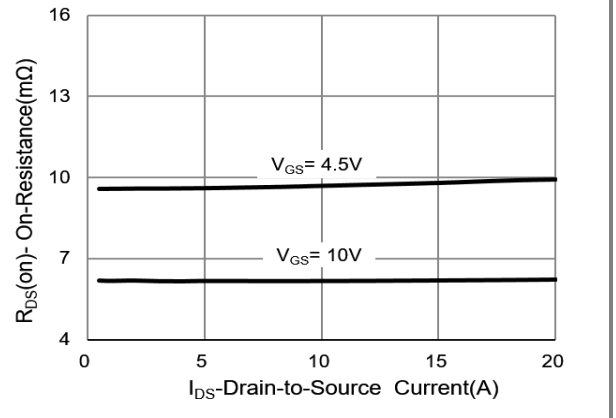

Fig.3 On-Resistance vs. Drain Current

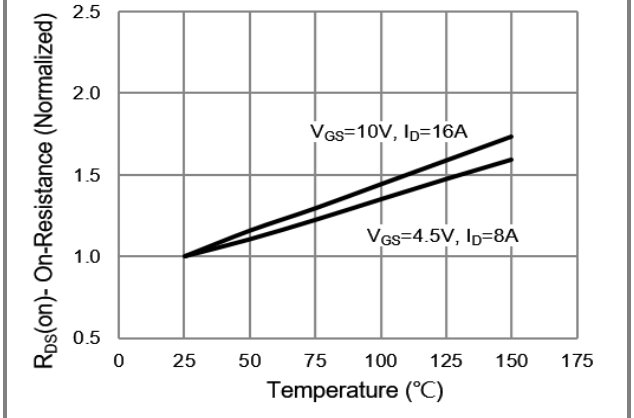

Fig.4 On-Resistance vs. Junction temperature

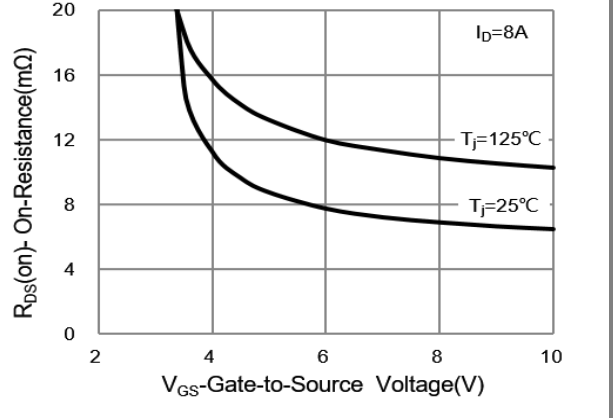

Fig.5 On-Resistance Variation with VGS.

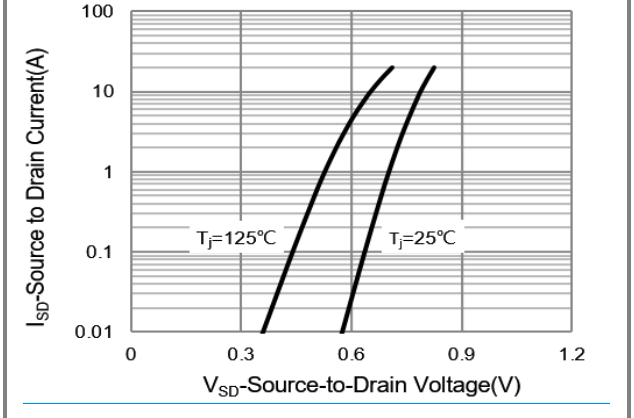

Fig.6 Source-Drain Diode Forward Voltage

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TYPICAL CHARACTERISTIC CURVES

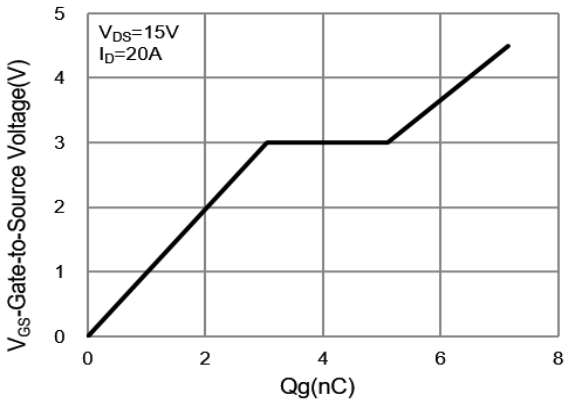

Fig.7 Gate-Charge Characteristics

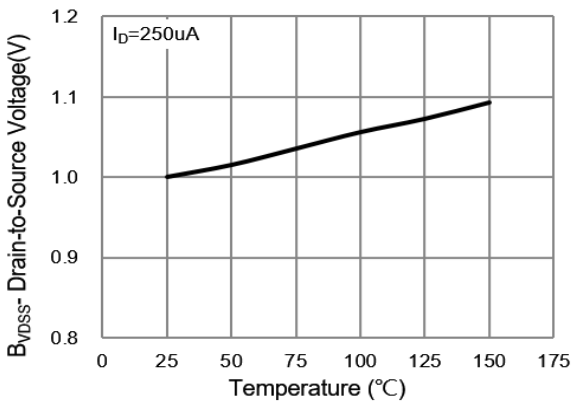

Fig.8 Breakdown Voltage Variation vs. Temperature.

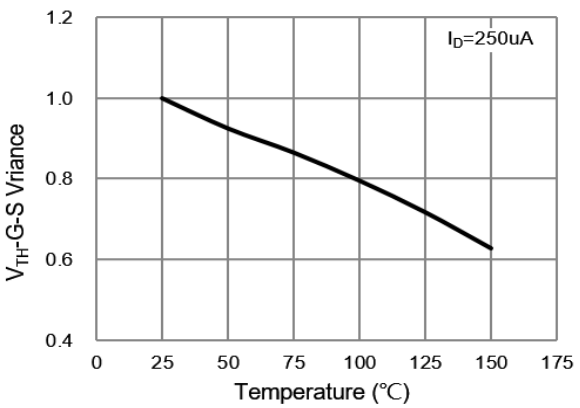

Fig.9 Threshold Voltage Variation with Temperature

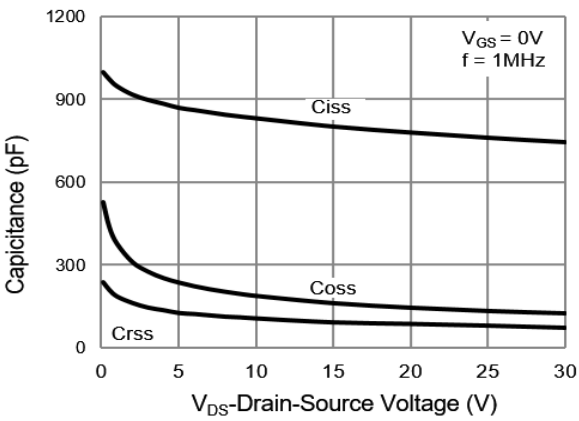

Fig.10 Capacitance vs. Drain-Source Voltage.

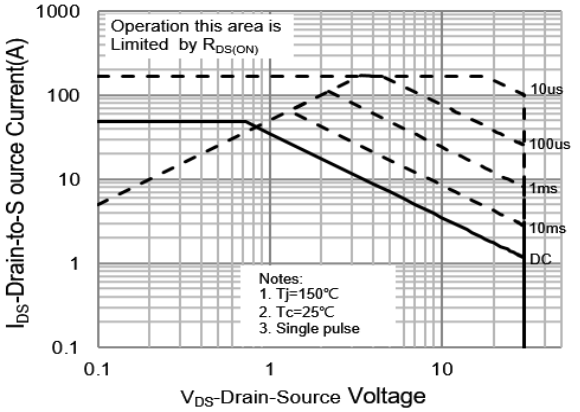

Fig.11 Maximum Safe Operating Area

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TYPICAL CHARACTERISTIC CURVES

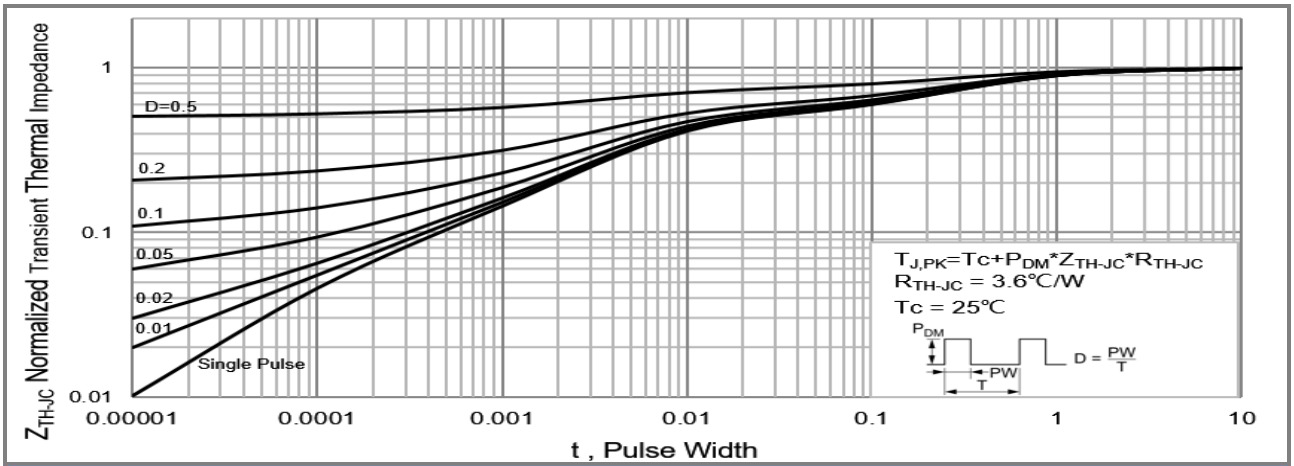


Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

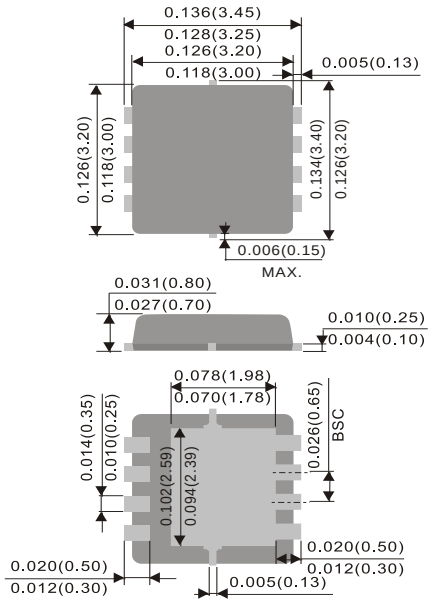
PJQ4408P

Part No Packing Code Version

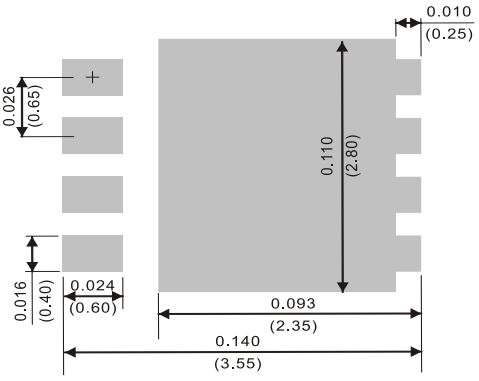
Part No Packing Code	Package Type	Packing Type	Marking	Version
PJQ4408P_R2_00001	DFN3333-8L	5K pcs / 13” reel	4408	Halogen free

Packaging Information & Mounting Pad Layout

DFN3333-8L Dimension — Unit: inch(mm)



DFN3333-8L Pad Layout — Unit: inch(mm)



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